

Document Title**64Kx8 bit Low Power and Low Voltage CMOS Static RAM****Revision History**

<u>Revision No.</u>	<u>History</u>	<u>Draft Data</u>	<u>Remark</u>
0.0	Design target	January 17, 1996	Advance
0.1	Initial draft - One datasheet for commercial, extended and industrial product. - Add 85ns part on KM68V512AFamily.	April 15, 1996	Preliminary
1.0	Finalize	June 17, 1996	Final
2.0	Revise - Add 32-sTSOP type package on product.	September 10, 1996	Final
3.0	Revise - Change datasheet format - Improve power dissipation 0.7 to 1.0W	February 12, 1998	Final

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64Kx8 bit Low Power and Low Voltage CMOS Static RAM

FEATURES

- Process Technology: Poly Load
- Organization: 64Kx8
- Power Supply Voltage
K6L0908V2A family: 2.7~3.3V
K6L0908U2A family: 3.0~3.3V
- Low Data Retention Voltage: 2V(Min)
- Three state output and TTL Compatible
- Package Type: 32-SOP-525, 32-TSOP1-0820F,
32-TSOP1-0813.4F

GENERAL DESCRIPTION

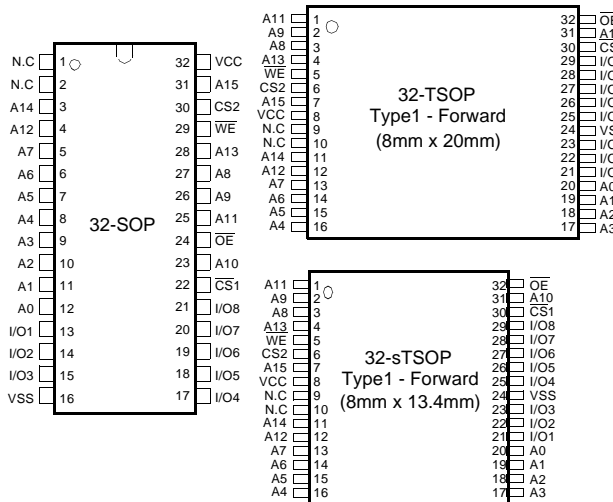
The K6L0908V2A and K6L0908U2A families are fabricated by SAMSUNG's advanced CMOS process technology. The families support various operating temperature ranges and have various package types for user flexibility of system design. The family also support low data retention voltage for battery back-up operation with low data retention current.

PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed	Power Dissipation		PKG Type
				Standby (I _{sb1} , Max)	Operating (I _{cc2} , Max)	
K6L0908V2A-B K6L0908U2A-B	Commercial(0~70°C)	3.0 ~ 3.6V	70 ¹ /85/100ns	10μA	40mA	32-SOP 32-TSOP1-F 32-sTSOP1-F
		2.7 ~ 3.3V	85 ¹ /100ns	10μA		
K6L0908V2A-D K6L0908U2A-D	Extended(-25~85°C)	3.0 ~ 3.6V	70 ¹ /85/100ns	20μA		
		2.7 ~ 3.3V	85 ¹ /100ns	15μA		
K6L0908V2A-F K6L0908U2A-F	Industrial (-40~85°C)	3.0 ~ 3.6V	70 ¹ /85/100ns	20μA		
		2.7 ~ 3.3V	85 ¹ /100ns	15μA		

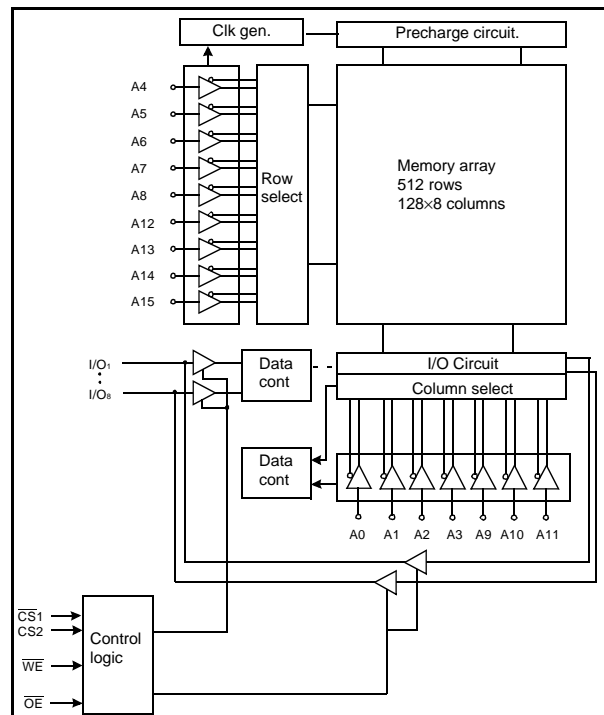
1. The parameter is measured with 30pF test load.

PIN DESCRIPTION



Name	Function
CS ₁ , CS ₂	Chip Select Inputs
\overline{OE}	Output Enable Input
\overline{WE}	Write Enable Input
A ₀ ~A ₁₅	Address Inputs
I/O ₁ ~I/O ₈	Data Inputs/Outputs
Vcc	Power
Vss	Ground
N.C	No Connection

FUNCTIONAL BLOCK DIAGRAM



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PRODUCT LIST

Commercial Temperature Products (0~70°C)		Extended Temperature Products (-25~85°C)		Industrial Temperature Products (-40~85°C)	
Part Name	Function	Part Name	Function	Part Name	Function
K6L0908V2A-GB70	32-SOP, 70ns, 3.3V, LL	K6L0908V2A-GD70	32-SOP, 70ns, 3.3V, LL	K6L0908V2A-GF70	32-SOP, 70ns, 3.3V, LL
K6L0908V2A-GB85	32-SOP, 85ns, 3.3V, LL	K6L0908V2A-GD85	32-SOP, 85ns, 3.3V, LL	K6L0908V2A-GF85	32-SOP, 85ns, 3.3V, LL
K6L0908V2A-GB10	32-SOP, 100ns, 3.3V, LL	K6L0908V2A-GD10	32-SOP, 100ns, 3.3V, LL	K6L0908V2A-GF10	32-SOP, 100ns, 3.3V, LL
K6L0908V2A-TB70	32-TSOP F, 70ns, 3.3V, LL	K6L0908V2A-TD70	32-TSOP F, 70ns, 3.3V, LL	K6L0908V2A-TF70	32-TSOP F, 70ns, 3.3V, LL
K6L0908V2A-TB85	32-TSOP F, 85ns, 3.3V, LL	K6L0908V2A-TD85	32-TSOP F, 85ns, 3.3V, LL	K6L0908V2A-TF85	32-TSOP F, 85ns, 3.3V, LL
K6L0908V2A-TB10	32-TSOP F, 100ns, 3.3V, LL	K6L0908V2A-TD10	32-TSOP F, 100ns, 3.3V, LL	K6L0908V2A-TF10	32-TSOP F, 100ns, 3.3V, LL
K6L0908V2A-YB70	32-sTSOP F, 70ns, 3.3V, LL	K6L0908V2A-YD70	32-sTSOP F, 70ns, 3.3V, LL	K6L0908V2A-YF70	32-sTSOP F, 70ns, 3.3V, LL
K6L0908V2A-YB85	32-sTSOP F, 85ns, 3.3V, LL	K6L0908V2A-YD85	32-sTSOP F, 85ns, 3.3V, LL	K6L0908V2A-YF85	32-sTSOP F, 85ns, 3.3V, LL
K6L0908V2A-YB10	32-sTSOP F, 100ns, 3.3V, LL	K6L0908V2A-YD10	32-sTSOP F, 100ns, 3.3V, LL	K6L0908V2A-YF10	32-sTSOP F, 100ns, 3.3V, LL
K6L0908U2A-GB85	32-SOP, 85ns, 3.0V, LL	K6L0908U2A-GD85	32-SOP, 85ns, 3.0V, LL	K6L0908U2A-GF85	32-SOP, 85ns, 3.0V, LL
K6L0908U2A-GB10	32-SOP, 100ns, 3.0V, LL	K6L0908U2A-GD10	32-SOP, 100ns, 3.0V, LL	K6L0908U2A-GF10	32-SOP, 100ns, 3.0V, LL
K6L0908U2A-TB85	32-TSOP F, 85ns, 3.0V, LL	K6L0908U2A-TD85	32-TSOP F, 85ns, 3.0V, LL	K6L0908U2A-TF85	32-TSOP F, 85ns, 3.0V, LL
K6L0908U2A-TB10	32-TSOP F, 100ns, 3.0V, LL	K6L0908U2A-TD10	32-TSOP F, 100ns, 3.0V, LL	K6L0908U2A-TF10	32-TSOP F, 100ns, 3.0V, LL
K6L0908U2A-YB85	32-sTSOP F, 85ns, 3.0V, LL	K6L0908U2A-YD85	32-sTSOP F, 85ns, 3.0V, LL	K6L0908U2A-YF85	32-sTSOP F, 85ns, 3.0V, LL
K6L0908U2A-YB10	32-sTSOP F, 100ns, 3.0V, LL	K6L0908U2A-YD10	32-sTSOP F, 100ns, 3.0V, LL	K6L0908U2A-YF10	32-sTSOP F, 100ns, 3.0V, LL

FUNCTIONAL DESCRIPTION

CS ₁	CS ₂	OE	WE	I/O	Mode	Power
H	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	Deselected	Standby
X ¹⁾	L	X ¹⁾	X ¹⁾	High-Z	Deselected	Standby
L	H	H	H	High-Z	Output Disabled	Active
L	H	L	H	Dout	Read	Active
L	H	X ¹⁾	L	Din	Write	Active

1. X means don't care (Must be low or high state.)

ABSOLUTE MAXIMUM RATINGS¹⁾

Item	Symbol	Ratings	Unit	Remark
Voltage on any pin relative to V _{ss}	V _{IN} , V _{OUT}	-0.5 to V _{CC} +0.5	V	-
Voltage on V _{CC} supply relative to	V _{CC}	-0.3 to 4.6	V	-
Power Dissipation	P _D	1.0	W	-
Storage temperature	T _{STG}	-65 to 150	°C	-
Operating Temperature	T _A	0 to 70	°C	K6L0908V2A-B, K6L0908U2A-B
		-25 to 85	°C	K6L0908V2A-D, K6L0908U2A-D
		-40 to 85	°C	K6L0908V2A-F, K6L0908U2A-F
Soldering temperature and time	T _{SOLDER}	260°C, 10sec (Lead Only)	-	-

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS¹⁾

Item	Symbol	Product	Min	Typ	Max	Unit
Supply voltage	V _{CC}	K6L0908V2A Family	3.0	3.3	3.6	V
		K6L0908U2A Family	2.7	3.0	3.3	V
Ground	V _{SS}	All Family	0	0	0	V
Input high voltage	V _{IH}	K6L0908V2A, K6L0908U2A Family	2.2	-	V _{CC} +0.3V ²⁾	V
Input low voltage	V _{IL}	K6L0908V2A, K6L0908U2A Family	-0.3 ³⁾	-	0.4	V

Note:

- Commercial Product : T_A=0 to 70°C, otherwise specified
 Extended Product : T_A=-25 to 85°C, otherwise specified
 Industrial Product : T_A=-40 to 85°C, otherwise specified
- Overshoot : V_{CC}+3.0V in case of pulse width≤30ns
- Undershoot : -3.0V in case of pulse width≤30ns
- Overshoot and undershoot are sampled, not 100% tested

CAPACITANCE¹⁾ (f=1MHz, T_A=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C _{IN}	V _{IN} =0V	-	6	pF
Input/Output capacitance	C _{IO}	V _{IO} =0V	-	8	pF

- Capacitance is sampled, not 100% tested

DC AND OPERATING CHARACTERISTICS

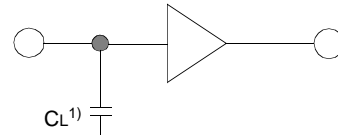
Item	Symbol	Test Conditions	Min	Typ	Max	Unit	
Input leakage current	I _{LI}	V _{IN} =V _{SS} to V _{CC}	-1	-	1	μA	
Output leakage current	I _{LO}	$\overline{CS}_1=V_{IH}$ or $\overline{CS}_2=V_{IL}$ or $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$, V _{IO} =V _{SS} to V _{CC}	-1	-	1	μA	
Operating power supply current	I _{CC}	I _{IO} =0mA, $\overline{CS}_1=V_{IL}$, $\overline{CS}_2=V_{IH}$, V _{IN} =V _{IH} or V _{IL}	-	-	5	mA	
Average operating current	I _{CC1}	Cycle time=1μs, 100% duty, I _{IO} =0mA, $\overline{CS}_1 \leq 0.2V$, $\overline{CS}_2 \geq V_{CC}-0.2V$, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	-	-	5	mA	
	I _{CC2}	Cycle time=Min, 100% duty, I _{IO} =0mA, $\overline{CS}_1=V_{IL}$, $\overline{CS}_2=V_{IH}$, V _{IN} =V _{IL} or V _{IH}	-	-	40	mA	
Output low voltage	V _{OL}	I _{OL} =2.1mA	-	-	0.4	V	
Output high voltage	V _{OH}	I _{OH} =-1.0mA	2.4	-	-	V	
Standby Current(TTL)	I _{SB}	$\overline{CS}_1=V_{IH}$, $\overline{CS}_2=V_{IL}$, Other inputs=V _{IL} or V _{IH}	-	-	0.3	mA	
Standby Current(CMOS)	I _{SB1}	$\overline{CS}_1 \geq V_{CC}-0.2V$, $\overline{CS}_2 \geq V_{CC}-0.2V$, or $\overline{CS}_2 \leq 0.2V$. Other inputs=0-V _{CC}	K6L0908V2A-B	-	-	10	μA
			K6L0908V2A-D K6L0908V2A-F	-	-	20	μA
			K6L0908U2A-B	-	-	10	μA
			K6L0908U2A-D K6L0908U2A-F	-	-	15	μA

AC OPERATING CONDITIONS

TEST CONDITIONS (Test Load and Input/Output Reference)

- Input pulse level : 0.4 to 2.2V
- Input rising and falling time : 5ns
- Input and output reference voltage : 1.5V
- Output load(see right) : $C_L=100pF+1TTL$
¹⁾ $C_L=30pF+1TTL$

1. K6L0908V2A-70 Family, K6L0908U2A-85 Family



1. Including scope and jig capacitance

AC CHARACTERISTICS

(K6L0908V2B Family: $V_{CC}=3.0\sim 3.6V$, K6L0908U2B Family: $V_{CC}=2.7\sim 3.3V$,
 Commercial product: $T_A=0$ to $70^\circ C$, Extended product: $T_A=-25$ to $85^\circ C$, Industrial product: $T_A=-40$ to $85^\circ C$)

Parameter List		Symbol	Speed Bins						Units
			70ns		85ns		100ns		
			Min	Max	Min	Max	Min	Max	
Read	Read cycle time	t _{RC}	70	-	85	-	100	-	ns
	Address access time	t _{AA}	-	70	-	85	-	100	ns
	Chip select to output	t _{CO}	-	70	-	85	-	100	ns
	Output enable to valid output	t _{OE}	-	35	-	45	-	50	ns
	Chip select to low-Z output	t _{LZ}	10	-	10	-	10	-	ns
	Output enable to low-Z output	t _{OLZ}	5	-	5	-	5	-	ns
	Chip disable to high-Z output	t _{HZ}	0	25	0	30	0	30	ns
	Output disable to high-Z output	t _{OHZ}	0	25	0	20	0	20	ns
	Output hold from address change	t _{OH}	10	-	10	-	15	-	ns
Write	Write cycle time	t _{WC}	70	-	85	-	100	-	ns
	Chip select to end of write	t _{CW}	60	-	70	-	80	-	ns
	Address set-up time	t _{AS}	0	-	0	-	0	-	ns
	Address valid to end of write	t _{AW}	60	-	70	-	80	-	ns
	Write pulse width	t _{WP}	55	-	60	-	70	-	ns
	Write recovery time	t _{WR}	0	-	0	-	0	-	ns
	Write to output high-Z	t _{WHZ}	0	25	0	25	0	30	ns
	Data to write time overlap	t _{DW}	30	-	35	-	40	-	ns
	Data hold from write time	t _{DH}	0	-	0	-	0	-	ns
	End write to output low-Z	t _{OW}	5	-	5	-	5	-	ns

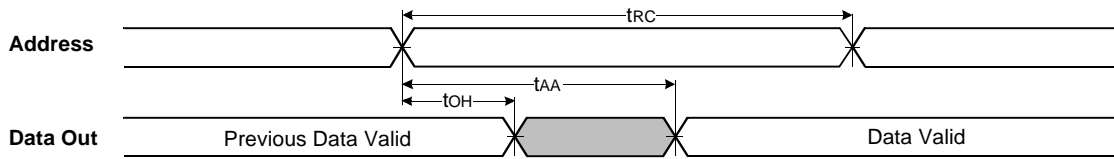
DATA RETENTION CHARACTERISTICS

Item	Symbol	Test Condition	Min	Typ	Max	Unit
V _{CC} for data retention	V _{DR}	$\overline{CS}_1^{1)} \geq V_{CC}-0.2V$	2.0	-	3.6	V
Data retention current	I _{DR}	$V_{CC}=3.0V, \overline{CS}_1 \geq V_{CC}-0.2V, CS_2 \geq V_{CC}-0.2V$ or $CS_2 \leq 0.2V$	-	-	10	μA
			-	-	15	
			-	-	15	
Data retention set-up time	t _{SDR}	See data retention waveform	0	-	-	ms
Recovery time	t _{RDR}		5	-	-	

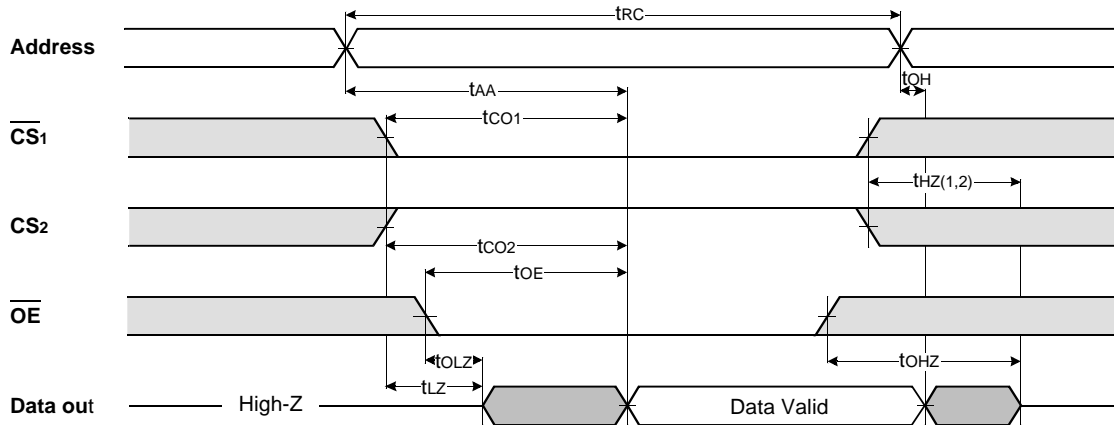
1. $\overline{CS}_1 \geq V_{CC}-0.2V, CS_2 \geq V_{CC}-0.2V$ (\overline{CS}_1 controlled) or $CS_2 \leq 0.2V$ (CS_2 controlled)

TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS}_1 = \overline{OE} = V_{IL}$, $\overline{WE} = V_{IH}$)



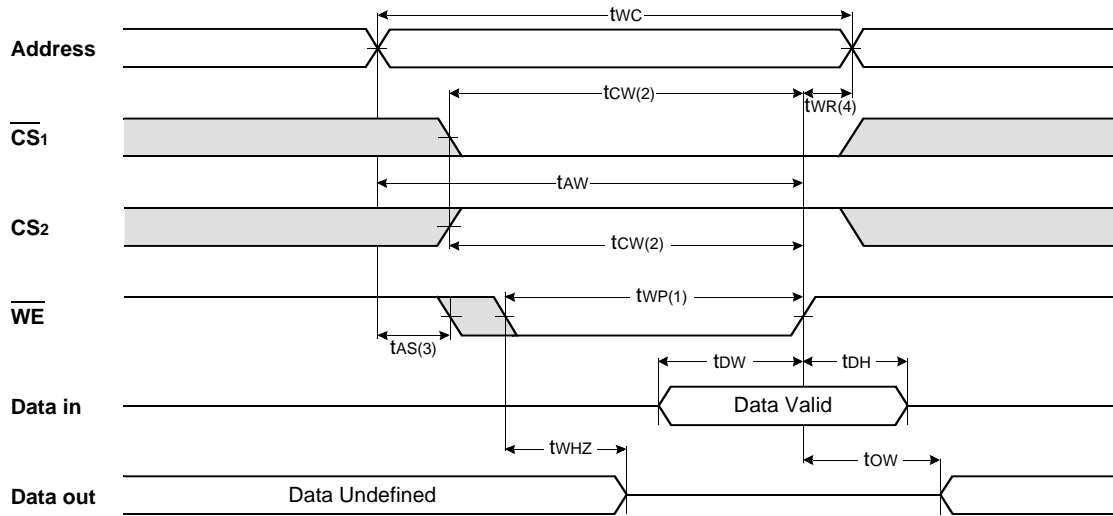
TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE} = V_{IH}$)



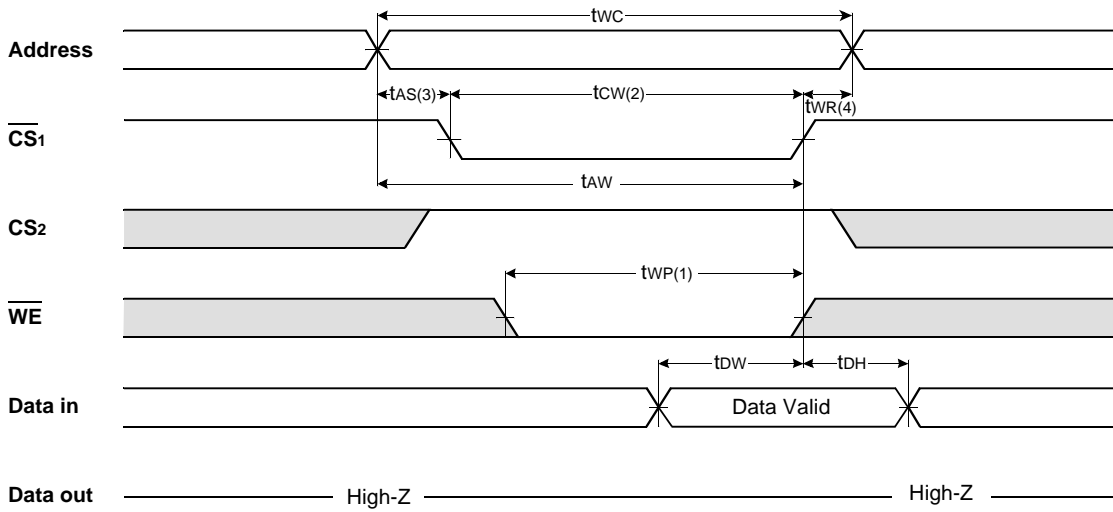
NOTES (READ CYCLE)

1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, $t_{HZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device interconnection.

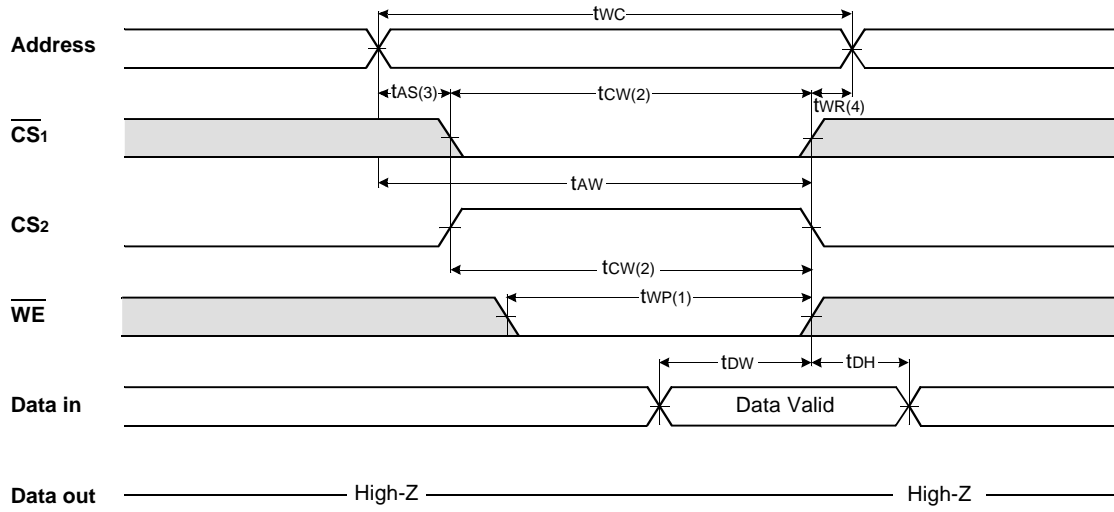
TIMING WAVEFORM OF WRITE CYCLE(1) (WE Controlled)



TIMING WAVEFORM OF WRITE CYCLE(2) ($\overline{CS1}$ Controlled)



TIMING WAVEFORM OF WRITE CYCLE(3) (\overline{CS}_1 Controlled)

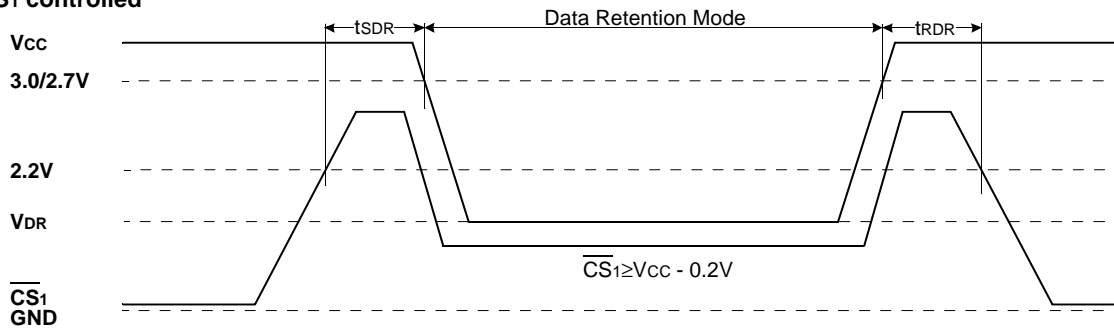


NOTES (WRITE CYCLE)

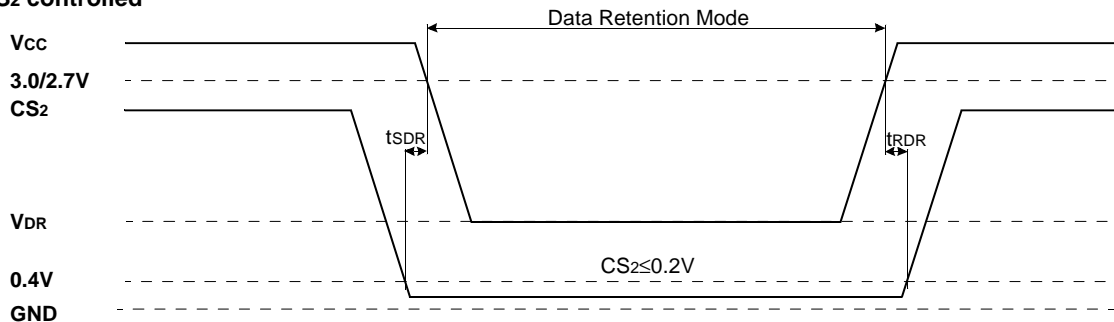
1. A write occurs during the overlap of a low \overline{CS}_1 , a high \overline{CS}_2 and a low \overline{WE} . A write begins at the latest transition among \overline{CS}_1 goes low, \overline{CS}_2 going high and \overline{WE} going low : A write ends at the earliest transition among \overline{CS}_1 going high, \overline{CS}_2 going low and \overline{WE} going high, t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from the \overline{CS}_1 going low or \overline{CS}_2 going high to the end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change. $t_{WR(1)}$ applied in case a write ends as \overline{CS}_1 or \overline{WE} going high $t_{WR(2)}$ applied in case a write ends as \overline{CS}_2 going to low.

DATA RETENTION WAVE FORM

\overline{CS}_1 controlled



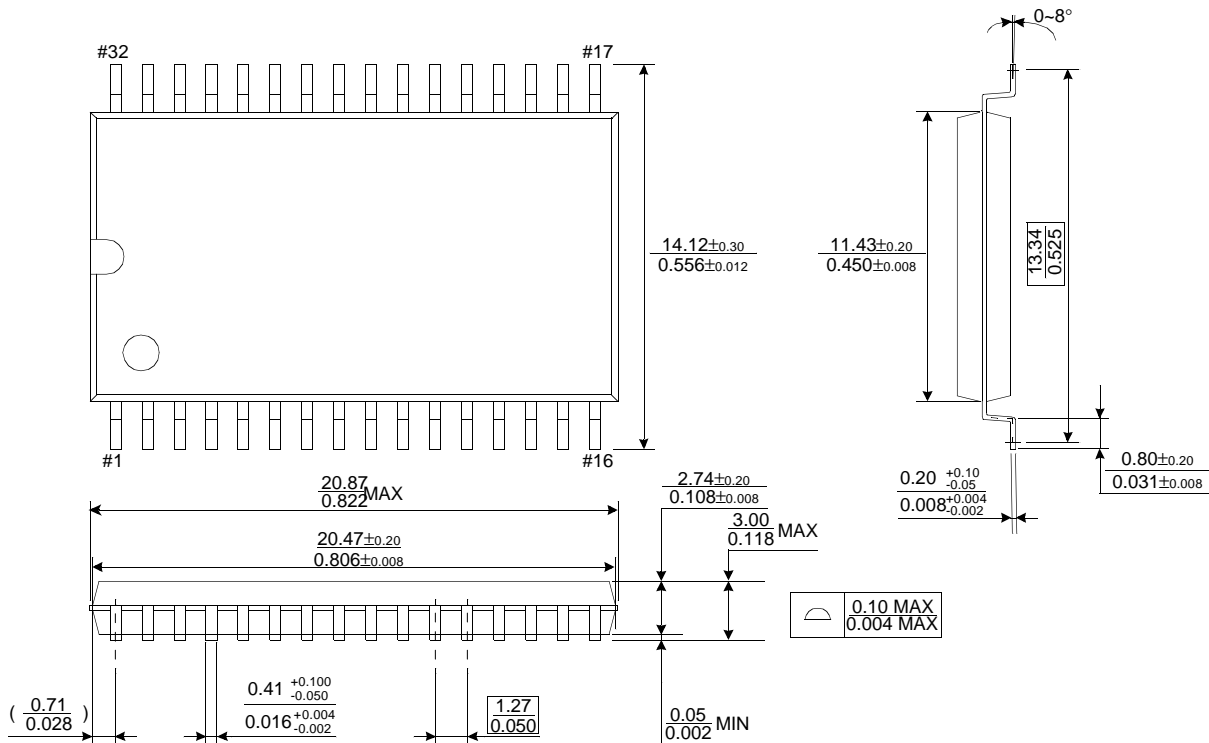
CS2 controlled



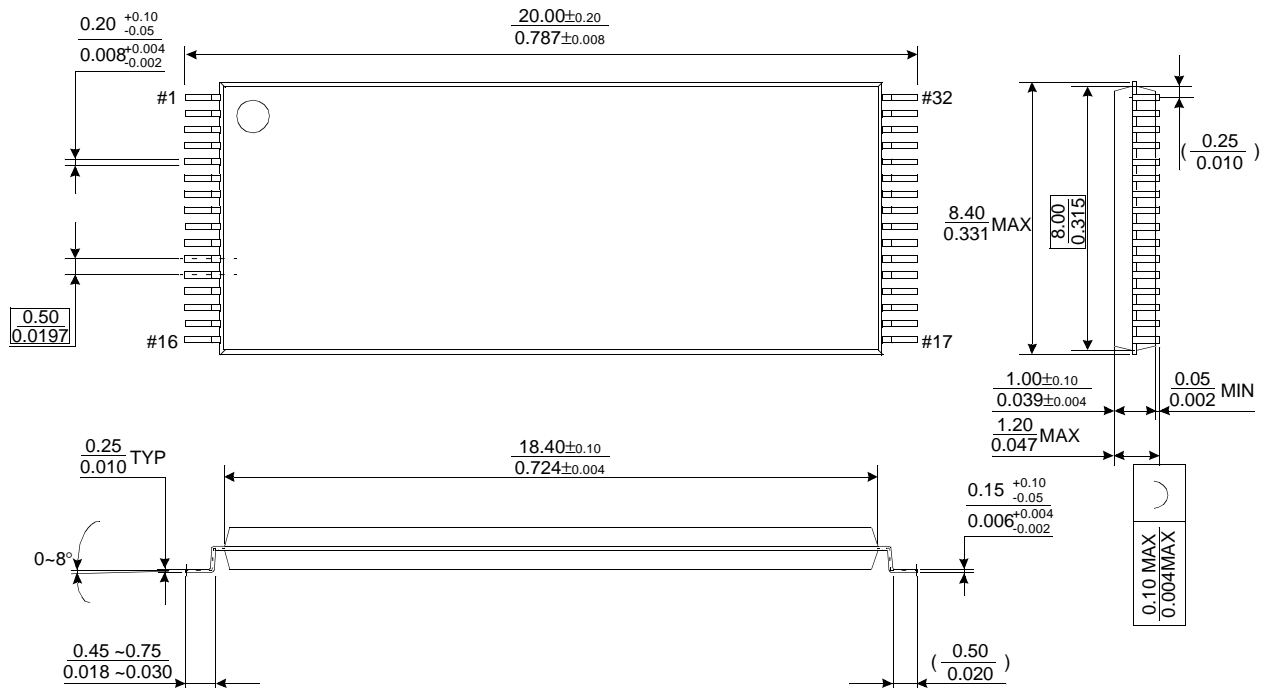
PACKAGE DIMENSIONS

Units: millimeter(inch)

32 PIN SMALL OUTLINE PACKAGE (525mil)



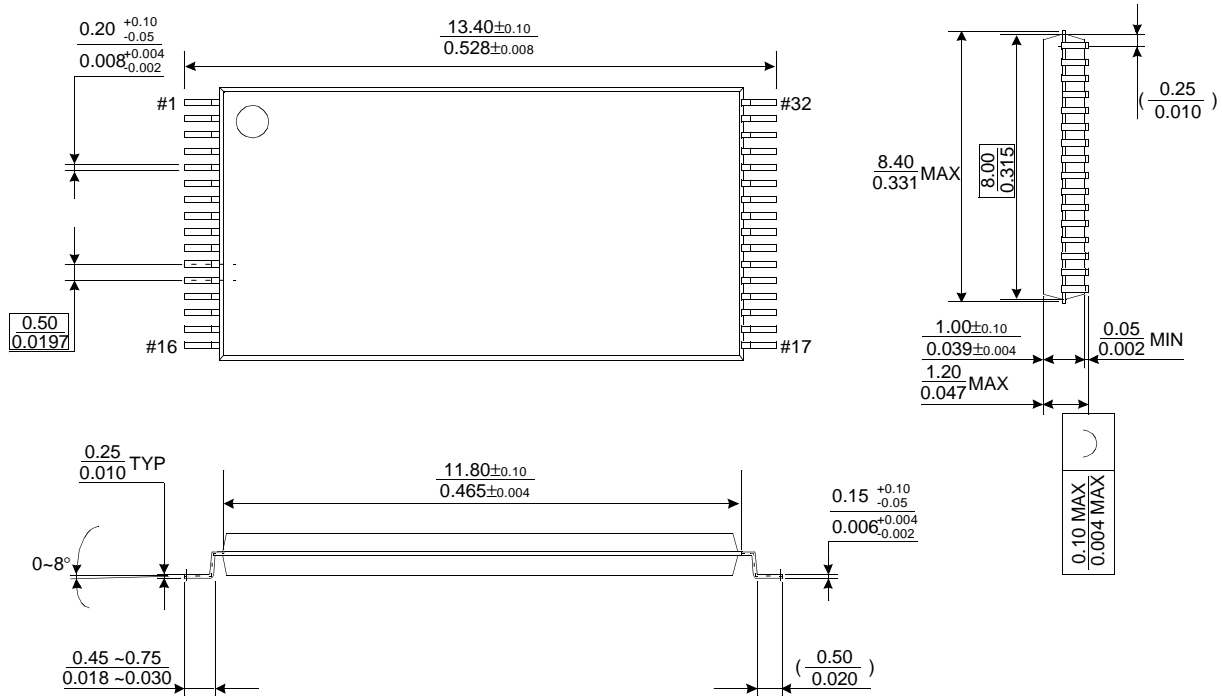
32 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0820F)



PACKAGE DIMENSIONS

Units: millimeter(inch)

32 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0813.4F)



32 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0813.4R)

